

# AOS Semiconductor Product Reliability Report

**AOW2500, rev A** 

**Plastic Encapsulated Device** 

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This AOS product reliability report summarizes the qualification result for AOW2500. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOW2500 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

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### I. Product Description:

The AOW2500 uses Trench MOSFET technology that is 150V uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of R<sub>DS(ON)</sub>, Ciss and Coss.

This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Details refer to the datasheet.

#### II. Die / Package Information:

AOW2500

Process Standard sub-micron

150V N-Channel MOSFET

Package TypeTO262Lead FrameBare CuDie AttachSoft solderBondingAl wire

Mold Material Epoxy resin with silica filler

Moisture Level Up to Level 1



#### III. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample size*	Number of Failures	Reference Standard
MSL Precondition	168hr 85°c/85%RH + 3 cycle reflow@260°c (MSL 1)	-	2772 pcs	0	JESD22-A113
нтдв	Temp = 150°c , Vgs=100% of Vgsmax	168 / 500 / 1000 hrs	616 pcs	0	JESD22-A108
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168 / 500 / 1000 hrs	616 pcs	0	JESD22-A108
HAST	130 °c , 85%RH, 33.3 psi, Vds = 80% of Vdsmax before arcing (typically ≤42V)	96 hrs	924 pcs	0	JESD22-A110
Pressure Pot	121°c , 29.7psi, RH=100%	96 hrs	924 pcs	0	JESD22-A102
Temperature Cycle	-65°c to 150°c , air to air,	250 / 500 cycles	924 pcs	0	JESD22-A104

<sup>\*</sup>Note: The reliability data presents total of available generic data up to the published date.

## IV. Reliability Evaluation

FIT rate (per billion): 3.27 MTTF = 34906 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =  $\text{Chi}^2 \times 10^9 \text{/} [2 \text{ (N) (H) (Af)}] = 3.27$ MTTF =  $10^9 / \text{FIT} = 34906 \text{ years}$ 

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

**Acceleration Factor ratio list:** 

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tis = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

 $\mathbf{k}$  = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K